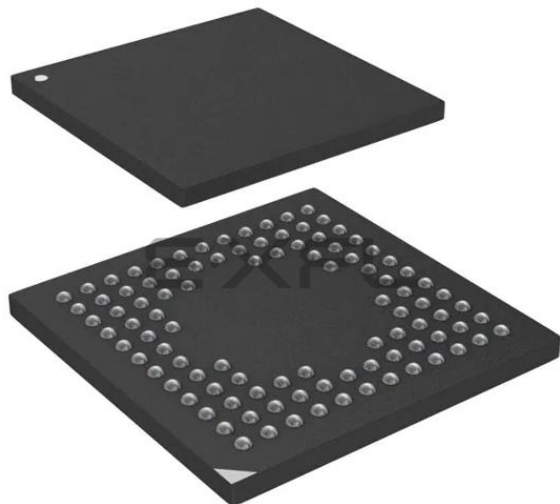




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I ² S, POR, PWM, WDT
Number of I/O	83
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 25x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-UFBGA
Supplier Device Package	100-UFBGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l151vch6tr

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Table 3. Functionalities depending on the operating power supply range (continued)

Operating power supply range	Functionalities depending on the operating power supply range			
	DAC and ADC operation	USB	Dynamic voltage scaling range	I/O operation
$V_{DD}=V_{DDA} = 2.0 \text{ to } 2.4 \text{ V}$	Conversion time up to 500 Ksps	Functional ⁽²⁾	Range 1, Range 2 or Range 3	Full speed operation
$V_{DD}=V_{DDA} = 2.4 \text{ to } 3.6 \text{ V}$	Conversion time up to 1 Msps	Functional ⁽²⁾	Range 1, Range 2 or Range 3	Full speed operation

1. CPU frequency changes from initial to final must respect " $F_{CPU \text{ initial}} < 4 * F_{CPU \text{ final}}$ " to limit V_{CORE} drop due to current consumption peak when frequency increases. It must also respect 5 μ s delay between two changes. For example to switch from 4.2 MHz to 32 MHz, the user can switch from 4.2 MHz to 16 MHz, wait 5 μ s, then switch from 16 MHz to 32 MHz.
2. Should be USB compliant from I/O voltage standpoint, the minimum V_{DD} is 3.0 V.

Table 4. CPU frequency range depending on dynamic voltage scaling

CPU frequency range	Dynamic voltage scaling range
16 MHz to 32 MHz (1ws) 32 kHz to 16 MHz (0ws)	Range 1
8 MHz to 16 MHz (1ws) 32 kHz to 8 MHz (0ws)	Range 2
2.1MHz to 4.2 MHz (1ws) 32 kHz to 2.1 MHz (0ws)	Range 3

Table 5. Functionalities depending on the working mode (from Run/active down to standby)

Ips	Run/Active	Sleep	Low-power Run	Low-power Sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
CPU	Y	--	Y	--	--	--	--	--
Flash	Y	Y	Y	Y	--	--	--	--
RAM	Y	Y	Y	Y	Y	--	--	--
Backup Registers	Y	Y	Y	Y	Y	--	Y	--
EEPROM	Y	Y	Y	Y	Y	--	--	--
Brown-out rest (BOR)	Y	Y	Y	Y	Y	Y	Y	--
DMA	Y	Y	Y	Y	--	--	--	--
Programmable Voltage Detector (PVD)	Y	Y	Y	Y	Y	Y	Y	--
Power On Reset (POR)	Y	Y	Y	Y	Y	Y	Y	--
Power Down Rest (PDR)	Y	Y	Y	Y	Y	--	Y	--
High Speed Internal (HSI)	Y	Y	--	--	--	--	--	--
High Speed External (HSE)	Y	Y	--	--	--	--	--	--
Low Speed Internal (LSI)	Y	Y	Y	Y	Y	--	Y	--
Low Speed External (LSE)	Y	Y	Y	Y	Y	--	Y	--
Multi-Speed Internal (MSI)	Y	Y	Y	Y	--	--	--	--
Inter-Connect Controller	Y	Y	Y	Y	--	--	--	--
RTC	Y	Y	Y	Y	Y	Y	Y	--
RTC Tamper	Y	Y	Y	Y	Y	Y	Y	Y
Auto WakeUp (AWU)	Y	Y	Y	Y	Y	Y	Y	Y
LCD	Y	Y	Y	Y	Y	--	--	--
USB	Y	Y	--	--	--	Y	--	--
USART	Y	Y	Y	Y	Y	(1)	--	--
SPI	Y	Y	Y	Y	--	--	--	--
I2C	Y	Y	Y	Y	--	(1)	--	--

3.9 LCD (liquid crystal display)

The LCD drives up to 8 common terminals and 44 segment terminals to drive up to 320 pixels.

- Internal step-up converter to guarantee functionality and contrast control irrespective of V_{DD} . This converter can be deactivated, in which case the V_{LCD} pin is used to provide the voltage to the LCD
- Supports static, 1/2, 1/3, 1/4 and 1/8 duty
- Supports static, 1/2, 1/3 and 1/4 bias
- Phase inversion to reduce power consumption and EMI
- Up to 8 pixels can be programmed to blink
- Unneeded segments and common pins can be used as general I/O pins
- LCD RAM can be updated at any time owing to a double-buffer
- The LCD controller can operate in Stop mode
- V_{LCD} rail decoupling capability

Table 6. V_{LCD} rail decoupling

	Bias			Pin	
	1/2	1/3	1/4		
$V_{LCDRAIL1}$	$1/2 V_{LCD}$	$2/3 V_{LCD}$	$1/2 V_{LCD}$	PB2	
$V_{LCDRAIL2}$	N/A	$1/3 V_{LCD}$	$1/4 V_{LCD}$	PB12	PE11
$V_{LCDRAIL3}$	N/A	N/A	$3/4 V_{LCD}$	PB0	PE12

3.10 ADC (analog-to-digital converter)

A 12-bit analog-to-digital converters is embedded into STM32L151xC and STM32L152xC devices with up to 25 external channels, performing conversions in single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs with up to 24 external channels in a group.

The ADC can be served by the DMA controller.

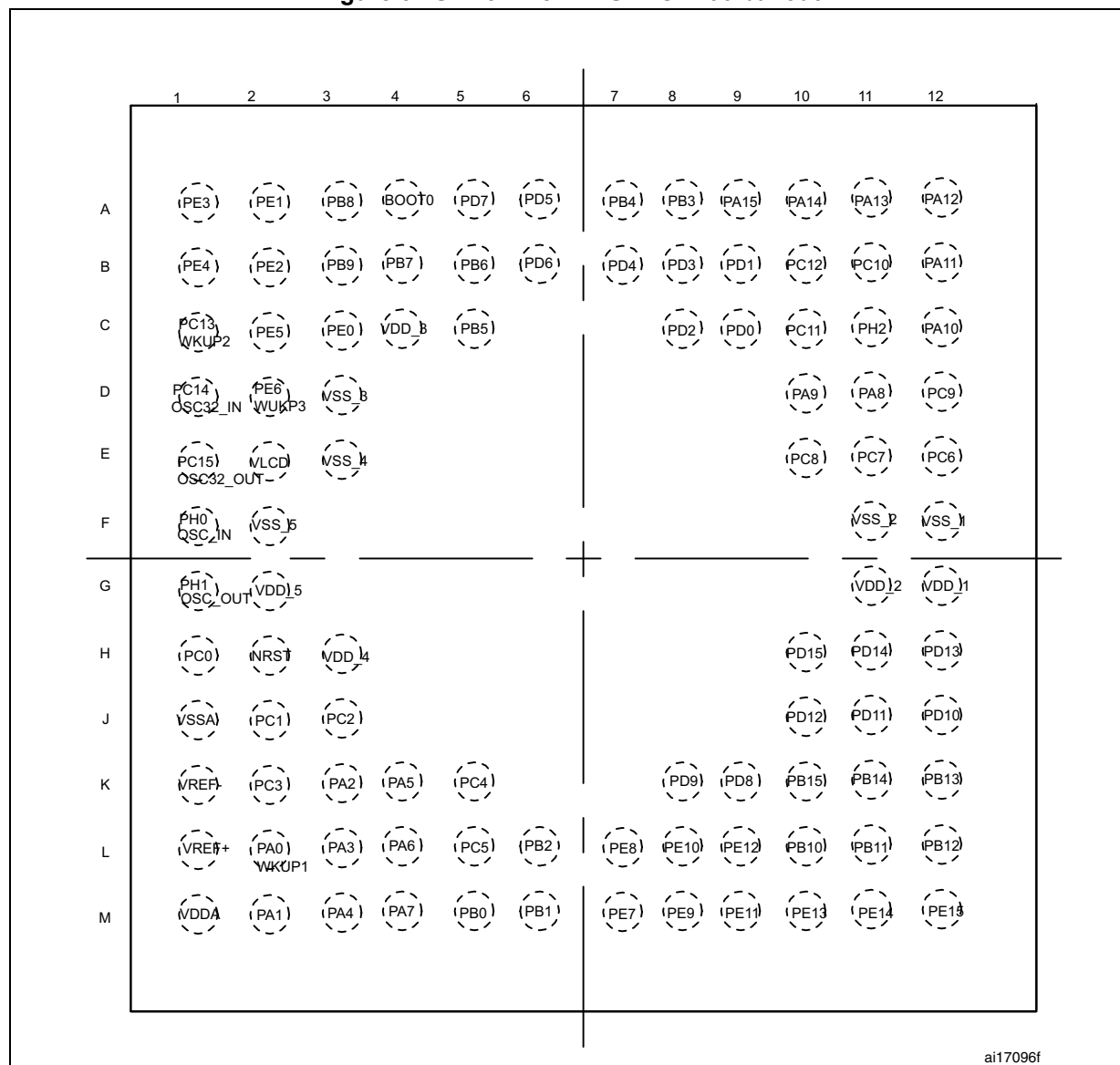
An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all scanned channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) can be internally connected to the ADC start triggers, to allow the application to synchronize A/D conversions and timers. An injection mode allows high priority conversions to be done by interrupting a scan mode which runs in as a background task.

The ADC includes a specific low-power mode. The converter is able to operate at maximum speed even if the CPU is operating at a very low frequency and has an auto-shutdown function. The ADC's runtime and analog front-end current consumption are thus minimized whatever the MCU operating mode.

4 Pin descriptions

Figure 3. STM32L15xVC UFBGA100 ballout



1. This figure shows the package top view.

Table 9. STM32L151xC and STM32L152xC pin definitions (continued)

Pins					Pin name	Pin type ⁽¹⁾	I / O Structure	Main function ⁽²⁾ (after reset)	Pin functions	
UFPGA100	LQFP100	LQFP64	WLCSP63	LQFP48 or UQFPN48					Alternate functions	Additional functions
C1	7	2	D5	2	PC13-WKUP2	I/O	FT	PC13	-	WKUP2/ RTC_TAMP1/ RTC_TS/RTC_OUT
D1	8	3	D7	3	PC14- OSC32_IN ⁽⁴⁾	I/O	TC	PC14	-	OSC32_IN
E1	9	4	D6	4	PC15- OSC32_OUT	I/O	TC	PC15	-	OSC32_OUT
F2	10	-	-	-	V _{SS_5}	S	-	V _{SS_5}	-	-
G2	11	-	-	-	V _{DD_5}	S	-	V _{DD_5}	-	-
F1	12	5	F6	5	PH0- OSC_IN ⁽⁵⁾	I/O	TC	PH0	-	OSC_IN
G1	13	6	F7	6	PH1- OSC_OUT ⁽⁵⁾	I/O	TC	PH1	-	OSC_OUT
H2	14	7	E7	7	NRST	I/O	RST	NRST	-	-
H1	15	8	E6	-	PC0	I/O	FT	PC0	LCD_SEG18	ADC_IN10/ COMP1_INP
J2	16	9	E5	-	PC1	I/O	FT	PC1	LCD_SEG19	ADC_IN11/ COMP1_INP
J3	17	10	G7	-	PC2	I/O	FT	PC2	LCD_SEG20	ADC_IN12/ COMP1_INP
K2	18	11	G6	-	PC3	I/O	TC	PC3	LCD_SEG21	ADC_IN13/ COMP1_INP
J1	19	12	F5	8	V _{SSA}	S	-	V _{SSA}	-	-
K1	20	-	-	-	V _{REF-}	S	-	V _{REF-}	-	-
L1	21	-	-	-	V _{REF+}	S	-	V _{REF+}	-	-
M1	22	13	H7	9	V _{DDA}	S	-	V _{DDA}	-	-
L2	23	14	E4	10	PA0-WKUP1	I/O	FT	PA0	TIM2_CH1_ETR/ TIM5_CH1/ USART2_CTS	WKUP1/ RTC_TAMP2/ ADC_IN0/ COMP1_INP

Table 9. STM32L151xC and STM32L152xC pin definitions (continued)

Pins					Pin name	Pin type ⁽¹⁾	I / O Structure	Main function ⁽²⁾ (after reset)	Pin functions	
UFPGA100	LQFP100	LQFP64	WLCSP63	LQFP48 or UQFPN48					Alternate functions	Additional functions
C10	79	52	A3	-	PC11	I/O	FT	PC11	SPI3_MISO/ USART3_RX/ LCD_SEG29/ LCD_SEG41/ LCD_COM5	-
B10	80	53	B4	-	PC12	I/O	FT	PC12	SPI3_MOSI/I2S3_SD/ USART3_CK/ LCD_SEG30/ LCD_SEG42/ LCD_COM6	-
C9	81	-	-	-	PD0	I/O	FT	PD0	TIM9_CH1/SPI2_NSS/ I2S2_WS	-
B9	82	-	-	-	PD1	I/O	FT	PD1	SPI2_SCK/I2S2_CK	-
C8	83	54	A4	-	PD2	I/O	FT	PD2	TIM3_ETR/LCD_SEG31/ LCD_SEG43/ LCD_COM7	-
B8	84	-	-	-	PD3	I/O	FT	PD3	SPI2_MISO/ USART2_CTS	-
B7	85	-	-	-	PD4	I/O	FT	PD4	SPI2_MOSI/I2S2_SD/ USART2_RTS	-
A6	86	-	-	-	PD5	I/O	FT	PD5	USART2_TX	-
B6	87	-	-	-	PD6	I/O	FT	PD6	USART2_RX	-
A5	88	-	-	-	PD7	I/O	FT	PD7	TIM9_CH2/USART2_CK	-
A8	89	55	C4	39	PB3	I/O	FT	JTDO	TIM2_CH2/SPI1_SCK/ SPI3_SCK/I2S3_CK/ LCD_SEG7/JTDO	COMP2_INM
A7	90	56	D4	40	PB4	I/O	FT	NJTRST	TIM3_CH1/SPI1_MISO/ SPI3_MISO/LCD_SEG8/ NJTRST	COMP2_INP
C5	91	57	A5	41	PB5	I/O	FT	PB5	TIM3_CH2/I2C1_SMBA/ SPI1_MOSI/SPI3_MOSI/ I2S3_SD/LCD_SEG9	COMP2_INP

Table 10. Alternate function input/output (continued)

Port name	Digital alternate function number											
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	AFIO11	AFIO14	AFIO15	
	Alternate function											
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3	LCD	CPRI	SYSTEM	
PB0	-	-	TIM3_CH3	-	-	-	-	-	SEG5	-	EVENT TOUT	
PB1	-	-	TIM3_CH4	-	-	-	-	-	SEG6	-	EVENT OUT	
PB2	BOOT1	-	-	-		-	-	-	-	-	EVENT OUT	
PB3	JTDO	TIM2_CH2	-	-	-	SPI1_SCK	SPI3_SCK I2S3_CK	-	SEG7	-	EVENT OUT	
PB4	NJTRST	-	TIM3_CH1	-	-	SPI1_MISO	SPI3_MISO	-	SEG8	-	EVENT OUT	
PB5	-	-	TIM3_CH2	-	I2C1_SMBA	SPI1_MOSI	SPI3_MOSI I2S3_SD	-	SEG9	-	EVENT OUT	
PB6	-		TIM4_CH1	-	I2C1_SCL	-	-	USART1_TX	-	-	EVENT OUT	
PB7	-	-	TIM4_CH2	-	I2C1_SDA	-	-	USART1_RX	-	-	EVENT OUT	
PB8	-	-	TIM4_CH3	TIM10_CH1	I2C1_SCL	-	-	-	SEG16	-	EVENT OUT	
PB9	-	-	TIM4_CH4	TIM11_CH1	I2C1_SDA	-	-	-	COM3	-	EVENT OUT	
PB10	-	TIM2_CH3	-	-	I2C2_SCL	-	-	USART3_TX	SEG10	-	EVENT OUT	
PB11	-	TIM2_CH4	-	-	I2C2_SDA	-	-	USART3_RX	SEG11	-	EVENT OUT	
PB12	-	-	-	TIM10_CH1	I2C2_SMBA	SPI2_NSS I2S2_WS	-	USART3_CK	SEG12	-	EVENT OUT	
PB13	-	-	-	TIM9_CH1	-	SPI2_SCK I2S2_CK	-	USART3_CTS	SEG13	-	EVENT OUT	
PB14	-	-	-	TIM9_CH2	-	SPI2_MISO	-	USART3_RTS	SEG14	-	EVENT OUT	
PB15	-	-	-	TIM11_CH1	-	SPI2_MOSI I2S2_SD	-	-	SEG15	-	EVENT OUT	
PC0	-	-	-	-	-	-	-	-	SEG18	TIMx_IC1	EVENT OUT	
PC1	-	-	-	-	-	-	-	-	SEG19	TIMx_IC2	EVENT OUT	
PC2	-	-	-	-	-	-	-	-	SEG20	TIMx_IC3	EVENT OUT	
PC3	-	-	-	-	-	-	-	-	SEG21	TIMx_IC4	EVENT OUT	

6.3.3 Embedded internal reference voltage

The parameters given in [Table 17](#) are based on characterization results, unless otherwise specified.

Table 16. Embedded internal reference voltage calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 30 °C ±5 °C V _{DDA} = 3 V ±10 mV	0x1FF8 00F8 - 0x1FF8 00F9

Table 17. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{REFINT} out ⁽¹⁾	Internal reference voltage	– 40 °C < T _J < +110 °C	1.202	1.224	1.242	V
I _{REFINT}	Internal reference current consumption	-	-	1.4	2.3	µA
T _{VREFINT}	Internal reference startup time	-	-	2	3	ms
V _{VREF_MEAS}	V _{DDA} and V _{REF+} voltage during V _{REFINT} factory measure	-	2.99	3	3.01	V
A _{VREF_MEAS}	Accuracy of factory-measured V _{REF} value ⁽²⁾	Including uncertainties due to ADC and V _{DDA} /V _{REF+} values	-	-	±5	mV
T _{Coeff} ⁽³⁾	Temperature coefficient	–40 °C < T _J < +110 °C	-	25	100	ppm/°C
A _{Coeff} ⁽³⁾	Long-term stability	1000 hours, T = 25 °C	-	-	1000	ppm
V _{DDC} coeff ⁽³⁾	Voltage coefficient	3.0 V < V _{DDA} < 3.6 V	-	-	2000	ppm/V
T _{S_vrefint} ⁽³⁾	ADC sampling time when reading the internal reference voltage	-	4	-	-	µs
T _{ADC_BUF} ^{(3) (4)}	Startup time of reference voltage buffer for ADC	-	-	-	10	µs
I _{BUF_ADC} ⁽³⁾	Consumption of reference voltage buffer for ADC	-	-	13.5	25	µA
I _{VREF_OUT} ⁽³⁾	VREF_OUT output current ⁽⁵⁾	-	-	-	1	µA
C _{VREF_OUT} ⁽³⁾	VREF_OUT output load	-	-	-	50	pF
I _{LPBUF} ⁽³⁾	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
V _{REFINT_DIV1} ⁽³⁾	1/4 reference voltage	-	24	25	26	% V _{REFINT}
V _{REFINT_DIV2} ⁽³⁾	1/2 reference voltage	-	49	50	51	
V _{REFINT_DIV3} ⁽³⁾	3/4 reference voltage	-	74	75	76	

1. Guaranteed by test in production.

2. The internal V_{REF} value is individually measured in production and stored in dedicated EEPROM bytes.

3. Guaranteed by characterization results.

4. Shortest sampling time can be determined in the application by multiple iterations.

Table 19. Current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditions		f _{HCLK}	Typ	Max ⁽¹⁾	Unit
I _{DD} (Run from RAM)	Supply current in Run mode, code executed from RAM, Flash switched off	f _{HSE} = f _{HCLK} up to 16 MHz, included f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	1 MHz	185	240	μA
				2 MHz	345	410	
				4 MHz	645	880 ⁽³⁾	
			Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	0.755	1.4	mA
				8 MHz	1.5	2.1	
				16 MHz	3	3.5	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	8 MHz	1.8	2.8	
				16 MHz	3.6	4.1	
				32 MHz	7.15	8.3	
		HSI clock source (16 MHz)	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	2.95	3.5	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	7.15	8.4	
		MSI clock, 65 kHz	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	65 kHz	38.5	85	μA
		MSI clock, 524 kHz		524 kHz	110	160	
		MSI clock, 4.2 MHz		4.2 MHz	690	810	

1. Guaranteed by characterization results, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

3. Guaranteed by test in production.

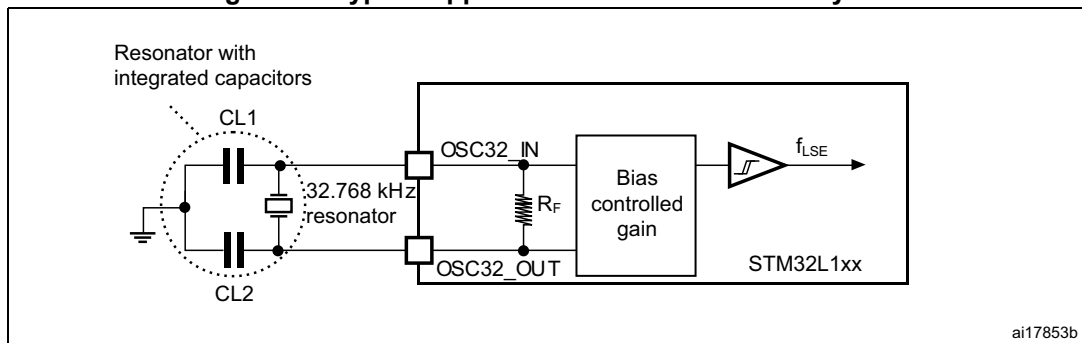
4. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Note: For C_{L1} and C_{L2} , it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator (see Figure 18). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

Caution: To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \leq 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.

Example: if the user chooses a resonator with a load capacitance of $C_L = 6$ pF and $C_{stray} = 2$ pF, then $C_{L1} = C_{L2} = 8$ pF.

Figure 18. Typical application with a 32.768 kHz crystal



ai17853b

6.3.8 PLL characteristics

The parameters given in [Table 34](#) are derived from tests performed under the conditions summarized in [Table 14](#).

Table 34. PLL characteristics

Symbol	Parameter	Value			Unit
		Min	Typ	Max ⁽¹⁾	
f _{PLL_IN}	PLL input clock ⁽²⁾	2	-	24	MHz
	PLL input clock duty cycle	45	-	55	%
f _{PLL_OUT}	PLL output clock	2	-	32	MHz
t _{LOCK}	PLL lock time PLL input = 16 MHz PLL VCO = 96 MHz	-	115	160	μs
Jitter	Cycle-to-cycle jitter	-	-	±600	ps
I _{DDA} (PLL)	Current consumption on V _{DDA}	-	220	450	μA
I _{DD} (PLL)	Current consumption on V _{DD}	-	120	150	

1. Guaranteed by characterization results.
2. Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL_OUT}.

6.3.9 Memory characteristics

The characteristics are given at T_A = -40 to 105 °C unless otherwise specified.

RAM memory

Table 35. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VRM	Data retention mode ⁽¹⁾	STOP mode (or RESET)	1.65	-	-	V

1. Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 41. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105\text{ }^{\circ}\text{C}$ conforming to JESD78A	II level A

6.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $-5\text{ }\mu\text{A}/+0\text{ }\mu\text{A}$ range), or other functional failure (for example reset occurrence oscillator frequency deviation, LCD levels).

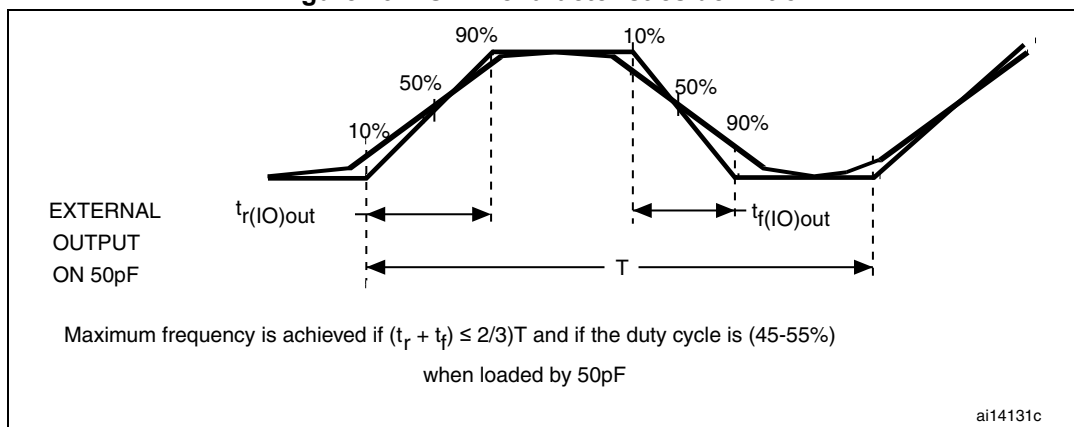
The test results are given in the [Table 42](#).

Table 42. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on all 5 V tolerant (FT) pins	-5 ⁽¹⁾	NA	mA
	Injected current on BOOT0	-0	NA	
	Injected current on any other pin	-5 ⁽¹⁾	+5	

1. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

Figure 19. I/O AC characteristics definition



6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see [Table 46](#))

Unless otherwise specified, the parameters given in [Table 46](#) are derived from tests performed under the conditions summarized in [Table 14](#).

Table 46. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}^{(1)}$	NRST input low level voltage	-	-	-	$0.3 V_{DD}$	V
$V_{IH(NRST)}^{(1)}$	NRST input high level voltage	-	$0.39V_{DD}+0.59$	-	-	
$V_{OL(NRST)}^{(1)}$	NRST output low level voltage	$I_{OL} = 2 \text{ mA}$ $2.7 \text{ V} < V_{DD} < 3.6 \text{ V}$	-	-	0.4	
		$I_{OL} = 1.5 \text{ mA}$ $1.65 \text{ V} < V_{DD} < 2.7 \text{ V}$	-	-		
$V_{hys(NRST)}^{(1)}$	NRST Schmitt trigger voltage hysteresis	-	-	$10\%V_{DD}^{(2)}$	-	mV
R_{PU}	Weak pull-up equivalent resistor ⁽³⁾	$V_{IN} = V_{SS}$	30	45	60	kΩ
$V_{F(NRST)}^{(1)}$	NRST input filtered pulse	-	-	-	50	ns
$V_{NF(NRST)}^{(3)}$	NRST input not filtered pulse	-	350	-	-	ns

1. Guaranteed by design.

2. With a minimum of 200 mV.

3. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

Table 53. USB: full speed electrical characteristics (continued)

Driver characteristics ⁽¹⁾					
Symbol	Parameter	Conditions	Min	Max	Unit
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage		1.3	2.0	V

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

I2S characteristics

Table 54. I2S characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I2S Main Clock Output		256 x 8K	256xFs ⁽¹⁾	MHz
f_{CK}	I2S clock frequency	Master data: 32 bits	-	64xFs	MHz
		Slave data: 32 bits	-	64xFs	
D_{CK}	I2S clock frequency duty cycle	Slave receiver, 48KHz	30	70	%
$t_{r(CK)}$	I2S clock rise time	Capacitive load CL=30pF	-	8	ns
$t_{f(CK)}$	I2S clock fall time			8	
$t_{v(WS)}$	WS valid time	Master mode	4	24	
$t_{h(WS)}$	WS hold time	Master mode	0	-	
$t_{su(WS)}$	WS setup time	Slave mode	15	-	
$t_{h(WS)}$	WS hold time	Slave mode	0	-	
$t_{su(SD_MR)}$	Data input setup time	Master receiver	8	-	
$t_{su(SD_SR)}$	Data input setup time	Slave receiver	9	-	
$t_{h(SD_MR)}$	Data input hold time	Master receiver	5	-	
$t_{h(SD_SR)}$		Slave receiver	4	-	
$t_{v(SD_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	64	
$t_{h(SD_ST)}$	Data output hold time	Slave transmitter (after enable edge)	22	-	
$t_{v(SD_MT)}$	Data output valid time	Master transmitter (after enable edge)	-	12	
$t_{h(SD_MT)}$	Data output hold time	Master transmitter (after enable edge)	8	-	

1. The maximum for 256xFs is 8 MHz

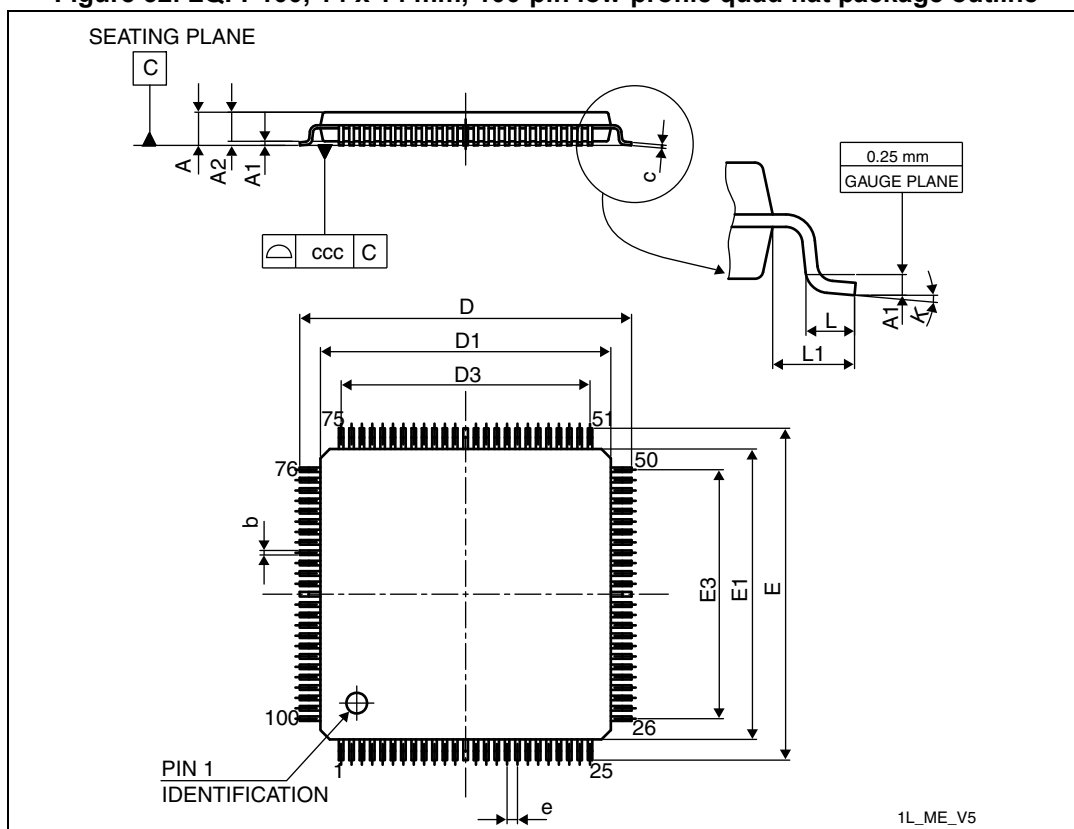
Note: Refer to the I2S section of the product reference manual for more details about the sampling frequency (Fs), f_{MCK} , f_{CK} and D_{CK} values. These values reflect only the digital peripheral behavior, source clock precision might slightly change them. D_{CK} depends mainly on the

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

7.1 LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package information

Figure 32. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package outline



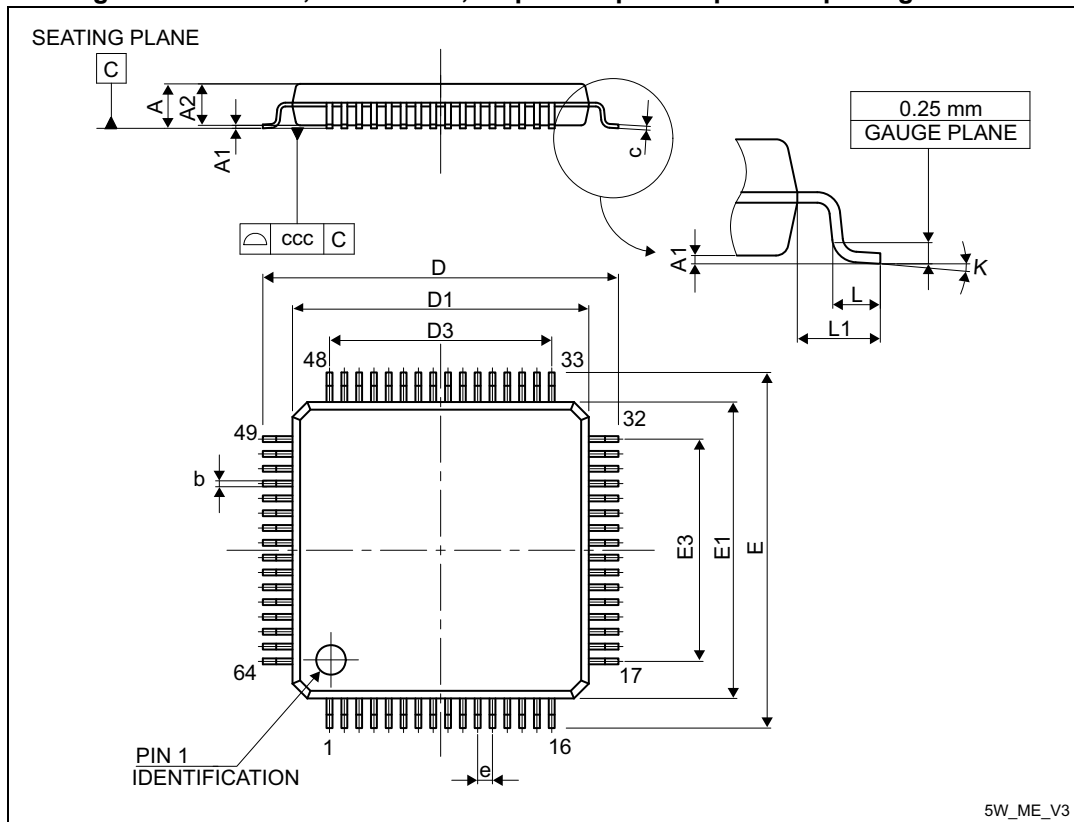
1. Drawing is not to scale.

Table 66. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571

7.2 LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package information

Figure 35. LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package outline



1. Drawing is not to scale.

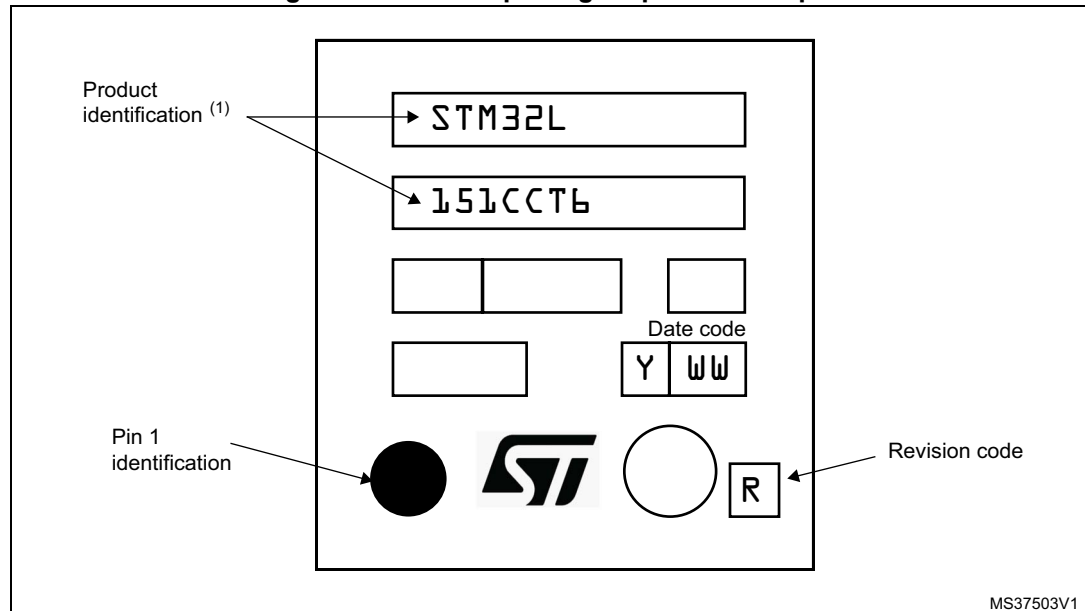
Table 67. LQFP64, 10 x 10 mm 64-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-

Marking of engineering samples

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 40. LQFP48 package top view example

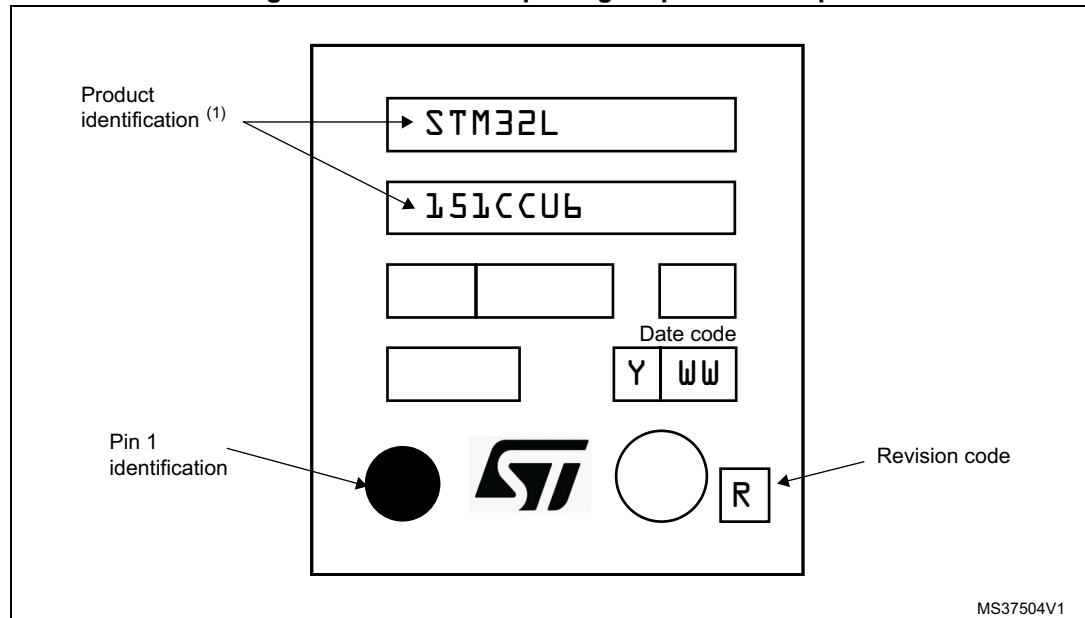


1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity

Marking of engineering samples

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 43. UFQFPN48 package top view example



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity

Figure 49. Thermal resistance suffix 6

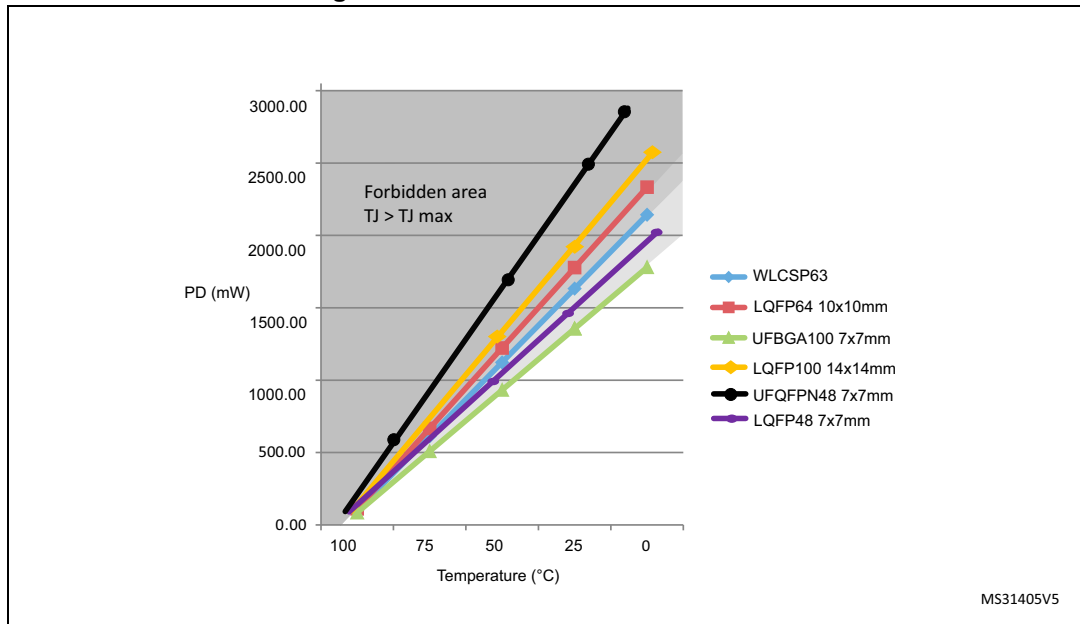
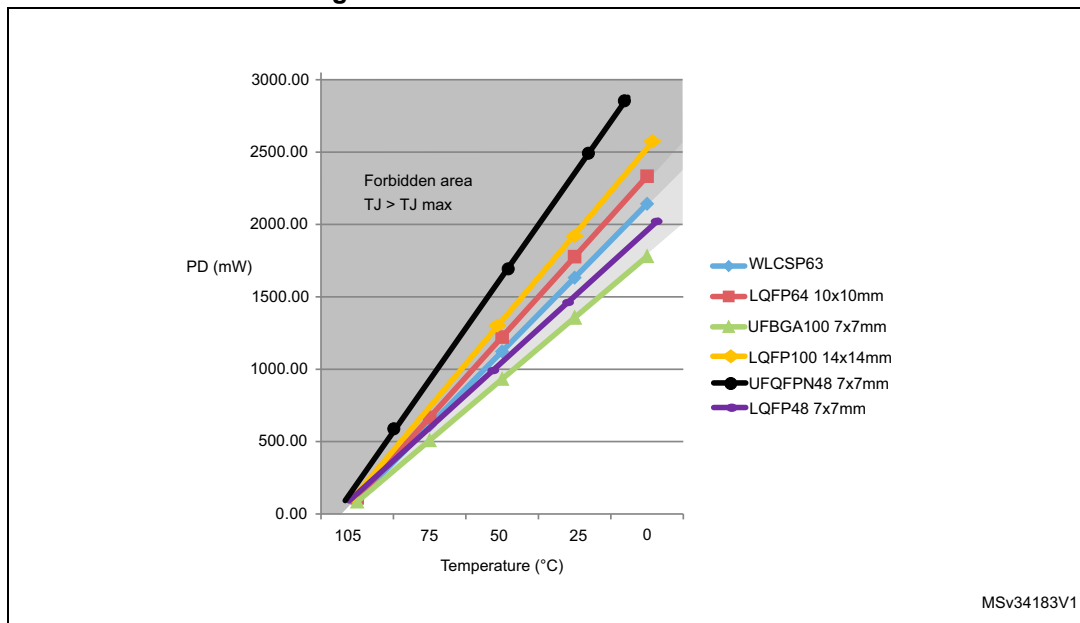


Figure 50. Thermal resistance suffix 7



7.7.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.